

AMENDMENT TO THE SPECIFICATION

*Please replace paragraph [0026] of the specification with the following amended paragraph [0026]:*

[0026] Figure 1e represents the process steps of Figures 1a-1d being repeated to form silicon oxide layer 60, low-k dielectric layer 65 including dummy fill shapes 70 (i.e., copper, aluminum or tungsten), and a silicon oxide layer 75 as is the case with layer 75 in Figure 3. These same processes can be continually repeated to form further layers, in accordance with the teachings of the invention.